ABSTRACT OF THE DISCLOSURE

Disclosed are a display system and a method of producing the same. In the present invention, a hexagonal pyramid shaped GaN semiconductor light-emitting device selectively crystal-grown is fixed on an upper surface of a substrate by embedding it in an insulation layer formed of an epoxy resin. Then the insulation layer is selectively dry etched in an oxygen plasma atmosphere to expose an upper end portion of the GaN semiconductor light-emitting device. A conductor film is formed on the entire surface, and a required portion of the conductor film is left as a lead-out electrode while the unrequired portion is removed by lithography.